[redacted]

[redacted] range	T_{stg}	-40-150	
[redacted]	[redacted]	[redacted]	[redacted]
[redacted]age (T_j=25)	V_{DRM}	800	V
[redacted]ge (T_j=25)	V_{RRM}	800	V
[redacted]07)	$I_{T(RMS)}$	1	A
[redacted]-state current [redacted])	I_{TSM}	25	A
[redacted]-state current [redacted])		27.5	
[redacted] T_j=25)	I^2t	3.125	A^2s

[redacted]

(T_j=25 unless otherwise specified)

Symbol	**Test Condition**	**Quadrant**	**Value**		**Unit**
I_{GT}	V_D=12V R_L=33	- -	MAX.	5	mA
				10	
V_{GT}		ALL	MAX.	1.3	V
V_{GD}	V_D=V				

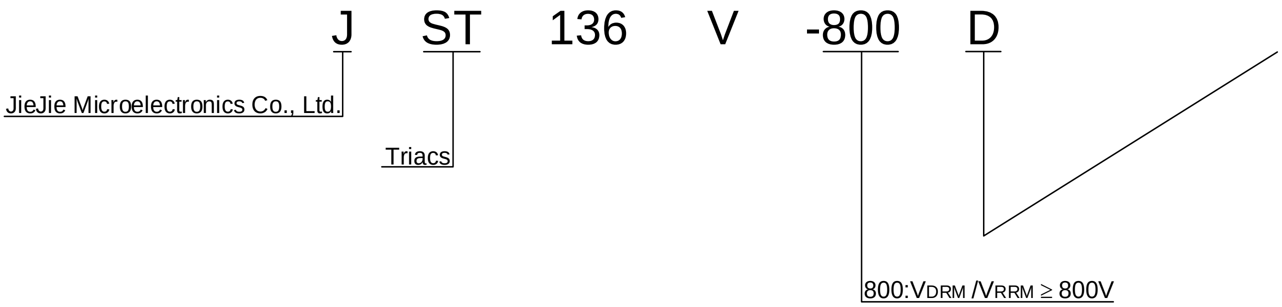
J
ST
136
V
-800
D
JieJie Microelectronics Co., Ltd.
Triacs
800:V_{DRM} /V_{RRM} ≥ 800V

FIG.1: Maximum power dissipation versus RMS on-state current

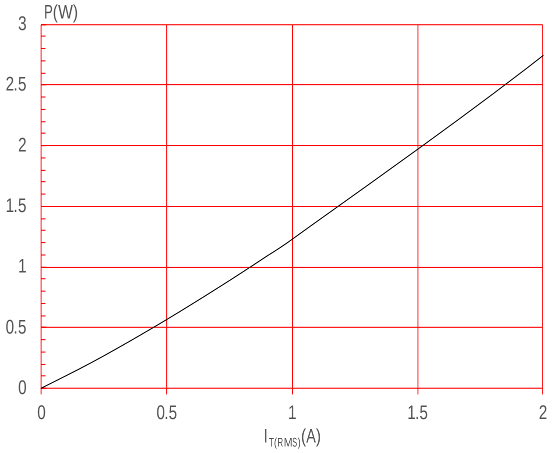

FIG.2: RMS on-state current versus case temperature

FIG.7: Relative variations of gate trigger current, holding current and latching current versus junction temperature

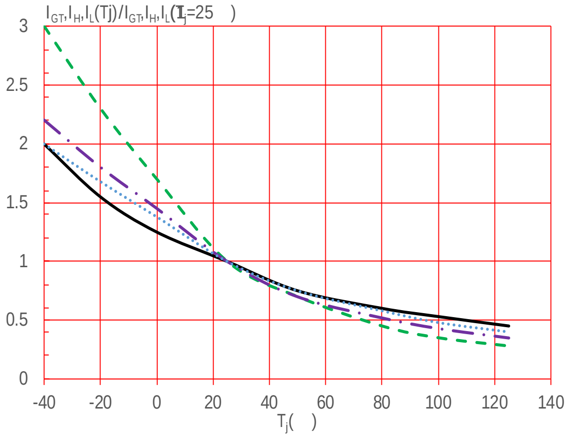

FIG.8 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)		Package	Base qty. (pcs)	Delivery mode
		- -				